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FORM**

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Total Number of Pages in This Submission

10

Patent Number

6,795,231 B1

19,634,179

Issue Date

September 21, 2004

First Named Inventor

Waclaw C. Koscielniak

Group Art Unit

2873

Examiner Name

Tuyen Q. Tra

Attorney Docket Number

100-15210 (P05000-D01)

ENCLOSURES (check all that apply)☐ Fee Transmittal Form☐ Fee Attached☐ Amendment/Response☐ After Final (Response)☐ Affidavits/declaration(s)☐ Extension of Time Request☐ Express Abandonment Request☐ Information Disclosure Statement☐ Certified Copy of Priority Document(s)☐ Response to Missing Parts/ Incomplete Application☐ Response to Missing Parts under 37 CFR 1.52 or 1.53☐ Assignment Papers (for an Application)☐ Drawing(s)☐ Licensing-related Papers☐ Petition Routing Slip (PTO/SB/69) and Accompanying Petition☐ Petition to Convert to a Provisional Application☐ Power of Attorney, Revocation Change of Correspondence Address☐ Terminal Disclaimer☒ Request for Certificate of Correction for PTO Mistakes☐ CD, Number of CD(s) _____☐ After Allowance Communication to Group☐ Appeal Communication to Board of Appeals and Interferences☐ Appeal Communication to Group (Appeal Notice, Brief, Reply Brief)☐ Proprietary Information☐ Status Letter☒ Other Enclosure(s) (please identify below):

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Mark C. Pickering, Reg. No. 36,239

Signature

Date

September 28, 2004

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September 28, 2004

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OCT 08 2004



PATENT

Attorney Docket No. 100-15210 [P05000-D01]

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent of)	Group Art Unit: 2873
Waclaw C. Koscielniak)	Examiner: Tuyen Q. Tra
U.S. Pat. No. 6,795,231 B1)	REQUEST FOR CERTIFICATE OF
Issued: September 21, 2004)	CORRECTION OF PATENT FOR PTO
)	<u>MISTAKES § 37 CFR 1.322(a)</u>
For: PHOTONIC CRYSTALS USING A)	
SEMICONDUCTOR-BASED)	
FABRICATION PROCESS (as)	
amended))	
)	
)	
)	

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Sir:

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The exact column and line number where the errors occur in the Patent is:

This Certificate is necessitated through fault of the U.S. Patent and Trademark Office and no fee is required.

On the Cover Page,

At (57) after "the Abstract" delete "6 Claims" and insert "--22 Claims--".

Claims 7-22 should be printed as follows:

--7. A photonic crystal formed on a semiconductor material of a first conductivity type, the semiconductor material having a top surface, the photonic crystal comprising:
a diffusion region of a second conductivity type formed in the semiconductor material; and
a plurality of spaced-apart stacks formed on the semiconductor material over the diffusion region, each stack having a plurality of layers of material and extending away from the top surface of the semiconductor material.

8. The crystal of claim 7 wherein the plurality of layers of material alternate between a first layer of material and a second layer of material, the first layer of material having a first dielectric constant, the second layer of material having a second dielectric constant.

OCT 08 2004

9. The crystal of claim 8 and further comprising an interstack material formed over the semiconductor material between and adjoining the plurality of stacks.

10. The crystal of claim 9 wherein the interstack material has a top surface that is substantially coplanar with a top surface of each stack.

11. The crystal of claim 9 wherein the interstack material has a top surface that lies below a top surface of each stack.

12. The crystal of claim 9 wherein the interstack material has a top surface that lies above a top surface of each stack.

13. The crystal of claim 7 and further comprising an interstack material formed over the semiconductor material between and adjoining the plurality of stacks, the interstack material having a top surface that is substantially coplanar with a top surface of each stack.

14. The crystal of claim 7 and further comprising an interstack material formed over the semiconductor material between and adjoining the plurality of stacks, the interstack material having a top surface that lies below a top surface of each stack.

15. The crystal of claim 7 and further comprising an interstack material formed over the semiconductor material between and adjoining the plurality of stacks, the interstack material having a top surface that lies above a top surface of each stack.

16. A photonic crystal formed on a semiconductor material of a conductivity type, the semiconductor material having a top surface, the photonic crystal comprising:
an array of spaced-apart stacks formed on the semiconductor material, each stack having a plurality of layers of material and extending away from the top surface of the semiconductor material, the plurality of layers of material alternating between a first layer of material and a second layer of material, the first layer of material having a first dielectric constant, the second layer of material having a second dielectric constant; and
an interstack material formed over the semiconductor material between and

adjoining the plurality of stacks.

17. The crystal of claim 16 wherein the interstack material has a top surface that is substantially coplanar with a top surface of each stack.

18. The crystal of claim 16 wherein the interstack material has a top surface that lies below a top surface of each stack.

19. The crystal of claim 16 wherein the interstack material has a top surface that lies above a top surface of each stack.

20. The crystal of claim 16 wherein the interstack material has a top surface that is substantially coplanar with a top surface of each stack.

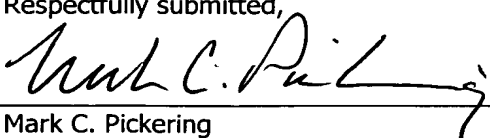
21. The crystal of claim 16 wherein the interstack material has a top surface that lies below a top surface of each stack.

22. The crystal of claim 16 wherein the interstack material has a top surface that lies above a top surface of each stack.--

Please send the Certificate to:

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Dated: 9-28-04

Respectfully submitted,

By: Mark C. Pickering
Mark C. Pickering
Reg. No. 36,239
Attorney for Assignee

**UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION**

PATENT NO: 6,795,231 B1

DATED: September 21, 2004

INVENTOR(S): Koscielniak

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On the Cover Page,

At (57) after "the Abstract" delete "6 Claims" and insert --22 Claims--.

Claims 7-22 should be printed as follows:

--7. A photonic crystal formed on a semiconductor material of a first conductivity type, the semiconductor material having a top surface, the photonic crystal comprising:

a diffusion region of a second conductivity type formed in the semiconductor material; and

a plurality of spaced-apart stacks formed on the semiconductor material over the diffusion region, each stack having a plurality of layers of material and extending away from the top surface of the semiconductor material.

8. The crystal of claim 7 wherein the plurality of layers of material alternate between a first layer of material and a second layer of material, the first layer of material having a first dielectric constant, the second layer of material having a second dielectric constant.

9. The crystal of claim 8 and further comprising an interstack material formed over the semiconductor material between and adjoining the plurality of stacks.

10. The crystal of claim 9 wherein the interstack material has a top surface that is substantially coplanar with a top surface of each stack.

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an array of spaced-apart stacks formed on the semiconductor material, each stack having a plurality of layers of material and extending away from the top surface of the semiconductor material, the plurality of layers of material alternating between a first layer of material and a second layer of material, the first layer of material having a first dielectric constant, the second layer of material having a second dielectric constant; and

an interstack material formed over the semiconductor material between and adjoining the plurality of stacks.

17. The crystal of claim 16 wherein the interstack material has a top surface that is substantially coplanar with a top surface of each stack.

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20. The crystal of claim 16 wherein the interstack material has a top surface that is substantially coplanar with a top surface of each stack.
21. The crystal of claim 16 wherein the interstack material has a top surface that lies below a top surface of each stack.
22. The crystal of claim 16 wherein the interstack material has a top surface that lies above a top surface of each stack.--

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an array of spaced-apart stacks formed on the semiconductor material, each stack having a plurality of layers of material and extending away from the top surface of the semiconductor material, the plurality of layers of material alternating between a first layer of material and a second layer of material, the first layer of material having a first dielectric constant, the second layer of material having a second dielectric constant; and

an interstack material formed over the semiconductor material between and adjoining the plurality of stacks.

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